

## INFORMATION DISCLOSURE CITATION IN AN APPLICATION

ATTY. DOCKET NO.  
61352-075

**SERIAL NO.**  
**10/817,035**

**APPLICANT**  
**Nobuyuki OTSUKA, et al.**

**FILING DATE**  
**April 05, 2004**

GROUP  
2811

(PTO-1449)

## U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
SWZ		JP 2003-289082 A	10-10-2002	MATSUSHITA ELECTRIC IND CO LTD	-	JAPAN (w/English Abstract)	
		JP 2000-91559 A	03-31-2000	FUJITSU LTD		JAPAN (w/English Abstract)	
		JP 2000-164852 A	06-16-2000	HITACHI CABLE, LTD		JAPAN (w/English Abstract)	
		JP 2002-94187 A	03-29-2002	HITACHI LTD		JAPAN (w/English Abstract)	
		JP 2000-216101 A	08-04-2000 A	SHARP CORP.		JAPAN (w/English Abstract)	
SWC		JP 2003-197644 A	07-11-2003	MATSUSHITA ELECTRIC INDUSTRIAL CO., LTD.		JAPAN (w/English Abstract)	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
SWC		HANG, D.R. et al., "Shubnikov-de Haas oscillations of two-dimensional electron gas in and in AsN/InGaAs single quantum well", <i>Semiconductor Science and Technology</i> , Vol. 17, no. 9, September 2002, pp. 999-1003
SWC		WANG, Jyh-Shyang et al., "Growth of InAsN/InGaAs (P) quantum wells on InP by gas source molecular beam epitaxy", <i>Journal of Vacuum Science &amp; Technology B</i> , Vol. 19, No. 1 January/February 2001, pp 202-206

**EXAMINER**

# CRANE

DATE CONSIDERED

9/02

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant).

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.